

## SILICON BRIDGE RECTIFIERS

## MB4F--MB10F

### FEATURES

- Glass: passivated chip junctions
- High surge overload rating: 30A peak
- Saves space on printed circuit boards
- High temperature soldering guaranteed: 260°C/10 seconds at 5 lbs. (2.3kg) tension



Lead-free

### MECHANICAL DATA

- Case: Molded plastic body over passivated junctions
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026

### Maximum Ratings (@T<sub>A</sub> = 25°C unless otherwise specified)

Characteristic	Symbol	MB4F	MB6F	MB8F	MB10F	UNITS
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	400	600	800	1000	V
RMS Reverse Voltage	V <sub>RMS</sub>	280	420	560	700	V
DC Blocking Voltage	V <sub>DC</sub>	400	600	800	1000	V
Maximum average forward Output current @T <sub>A</sub> =25°C	I <sub>F(AV)</sub>	0.8				A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I <sub>FSM</sub>	30				A

### Thermal Characteristics

Characteristic	Symbol	MB4F	MB6F	MB8F	MB10F	UNITS
Typical junction capacitance per leg (NOTE 1)	C <sub>J</sub>	8				p F
Operating junction temperature range	T <sub>J</sub>	- 55 ---- + 150				°C
Storage temperature range	T <sub>STG</sub>	- 55 ---- + 150				°C

### Electrical Characteristics (@T<sub>A</sub> = 25°C unless otherwise specified)

Characteristic	Symbol	MB4F	MB6F	MB8F	MB10F	UNITS
Maximum instantaneous forward voltage at 0.4 A	V <sub>F</sub>	1.0				V
Maximum reverse current @T <sub>A</sub> =25°C at rated DC blocking voltage @T <sub>A</sub> =100°C	I <sub>R</sub>	5.0 0.1				μ A m A

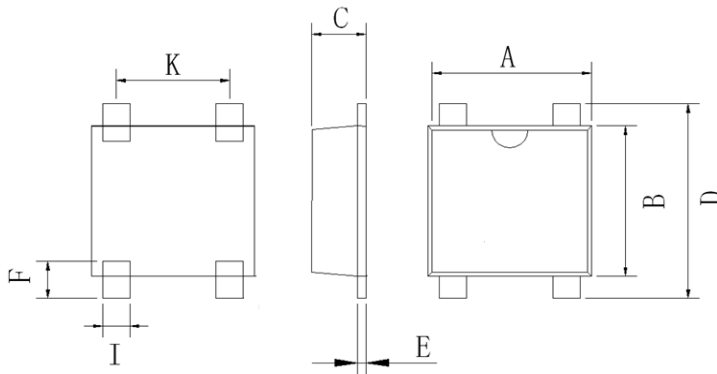
NOTES: (1) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts



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**PACKAGE OUTLINE DIMENSIONS**



MBF		
Dim	Min	Max
A	4.6	5
B	4.4	4.8
C	1.1	1.3
D	5.4	5.8
E	0.15	0.25
F	0.7	1.1
I	0.5	0.8
K	2.35	2.65
All Dimensions in mm		

**PACKAGE INFORMATION**

Device	Package	Shipping
MB4F--MB10F	MBF	5000/Tape&Reel



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